

Applications

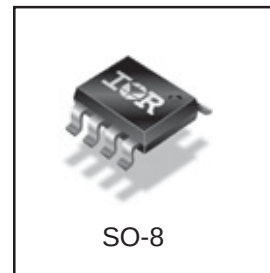
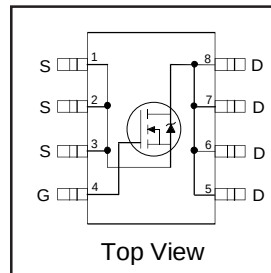
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Computer Processor Power
- Lead-Free

Benefits

- Ultra-Low Gate Impedance
- Very Low $R_{DS(on)}$
- Fully Characterized Avalanche Voltage and Current

HEXFET® Power MOSFET

V_{DSS}	$R_{DS(on)}$ max	I_D
30V	8.0m Ω	14A



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 30	V
I_D @ $T_A = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	14	A
I_D @ $T_A = 70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	11	
I_{DM}	Pulsed Drain Current①	110	
P_D @ $T_A = 25^\circ\text{C}$	Maximum Power Dissipation③	2.5	W
P_D @ $T_A = 70^\circ\text{C}$	Maximum Power Dissipation③	1.6	W
	Linear Derating Factor	0.02	mW/ $^\circ\text{C}$
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	$^\circ\text{C}$

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	—	20	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-Ambient ④	—	50	

Notes ① through ④ are on page 8

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.029	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	6.3	8.0	m Ω	$V_{GS} = 16V, I_D = 14A$ ③
		—	7.0	9.0		$V_{GS} = 10V, I_D = 11A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 24V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -24V$

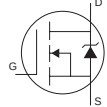
Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

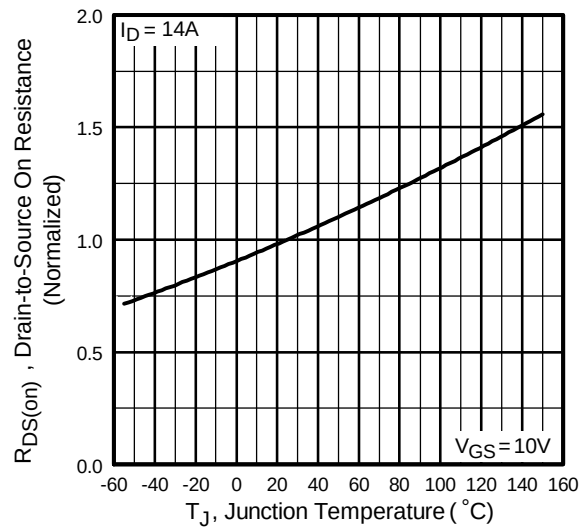
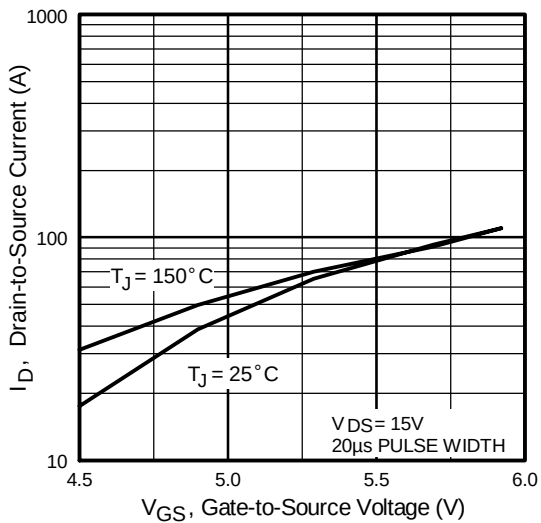
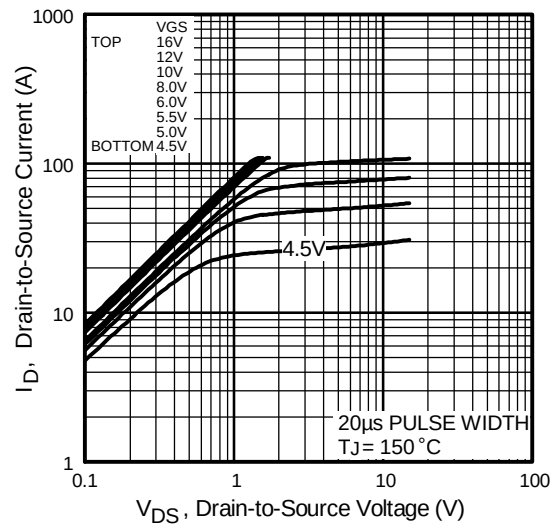
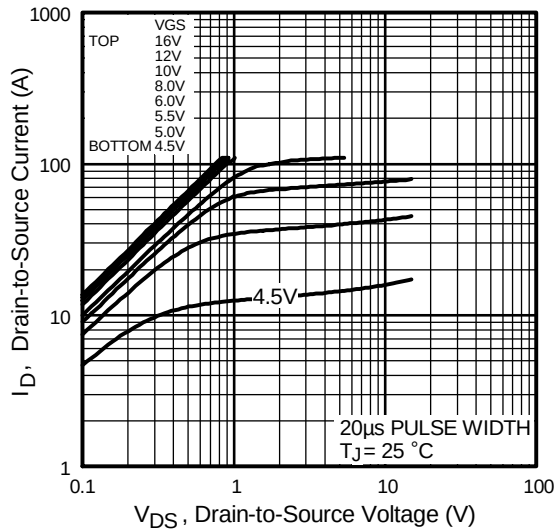
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	26	—	—	S	$V_{DS} = 15V, I_D = 11A$
Q_g	Total Gate Charge	—	39	59	nC	$I_D = 11A$
Q_{gs}	Gate-to-Source Charge	—	11	17		$V_{DS} = 15V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	8.7	13		$V_{GS} = 10V$ ③
Q_{oss}	Output Gate Charge	—	29	44		$V_{GS} = 0V, V_{DS} = 16V$
$t_{d(on)}$	Turn-On Delay Time	—	10	—	ns	$V_{DD} = 15V$
t_r	Rise Time	—	4.6	—		$I_D = 11A$
$t_{d(off)}$	Turn-Off Delay Time	—	22	—		$R_G = 1.8\Omega$
t_f	Fall Time	—	5.0	—		$V_{GS} = 10V$ ③
C_{iss}	Input Capacitance	—	2410	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	1100	—		$V_{DS} = 15V$
C_{rss}	Reverse Transfer Capacitance	—	110	—		$f = 1.0MHz$

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	280	mJ
I_{AR}	Avalanche Current①	—	11	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	110		
V_{SD}	Diode Forward Voltage	—	0.82	1.3	V	$T_J = 25^\circ\text{C}, I_S = 11A, V_{GS} = 0V$ ③
		—	0.68	—		$T_J = 125^\circ\text{C}, I_S = 11A, V_{GS} = 0V$
t_{rr}	Reverse Recovery Time	—	51	77	ns	$T_J = 25^\circ\text{C}, I_F = 11A, V_R = 20V$
Q_{rr}	Reverse Recovery Charge	—	87	130	nC	$di/dt = 100A/\mu s$ ③
t_{rr}	Reverse Recovery Time	—	52	78	ns	$T_J = 125^\circ\text{C}, I_F = 11A, V_R = 20V$
Q_{rr}	Reverse Recovery Charge	—	93	140	nC	$di/dt = 100A/\mu s$ ③



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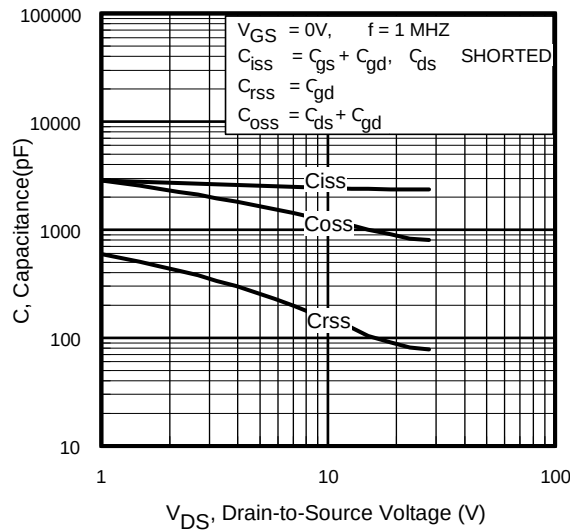


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

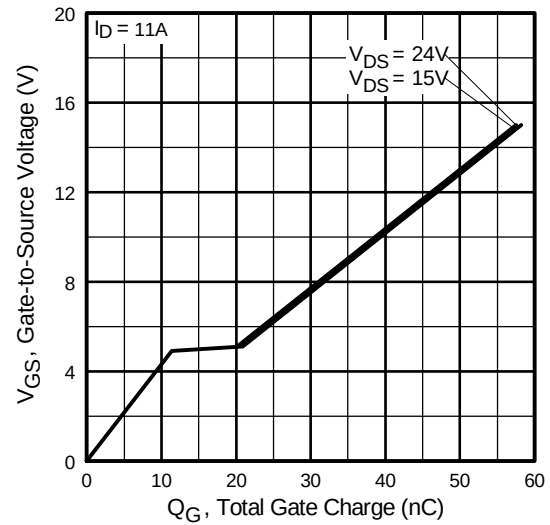


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

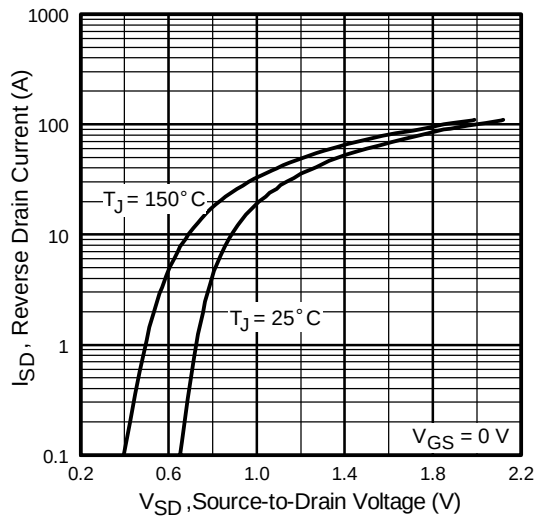


Fig 7. Typical Source-Drain Diode Forward Voltage

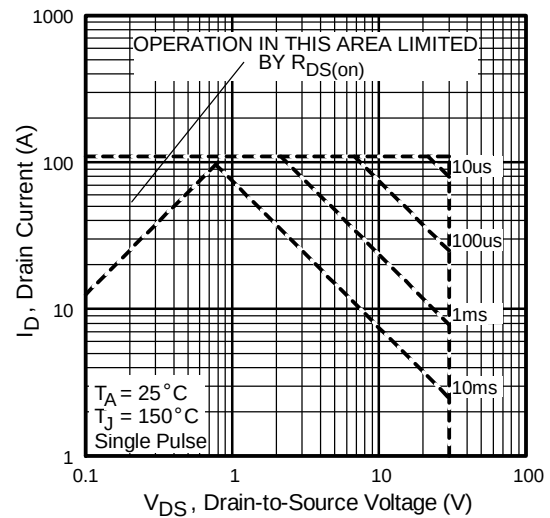


Fig 8. Maximum Safe Operating Area

Fig 6. On-Resistance Vs. Drain Current

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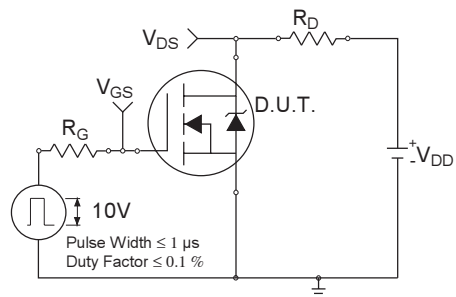
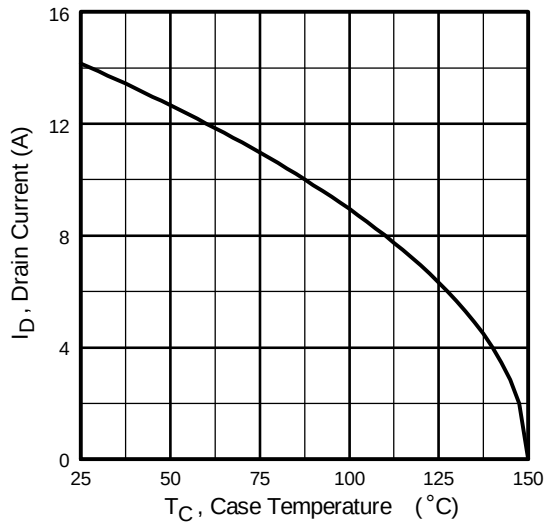


Fig 10a. Switching Time Test Circuit

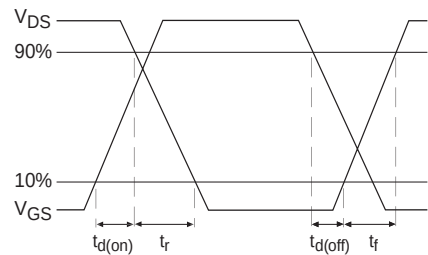


Fig 10b. Switching Time Waveforms

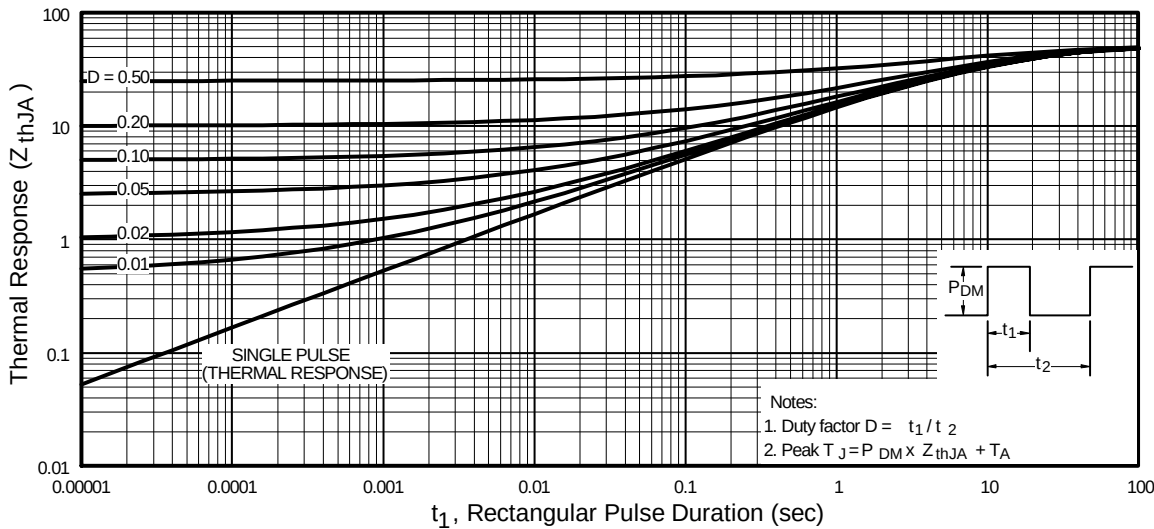


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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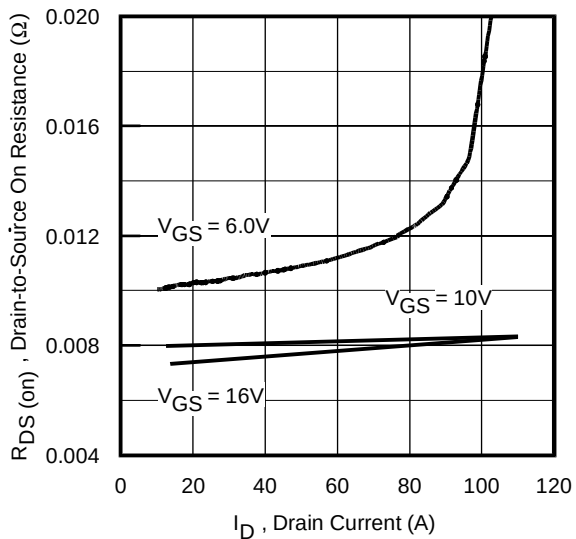


Fig 12. On-Resistance Vs. Drain Current

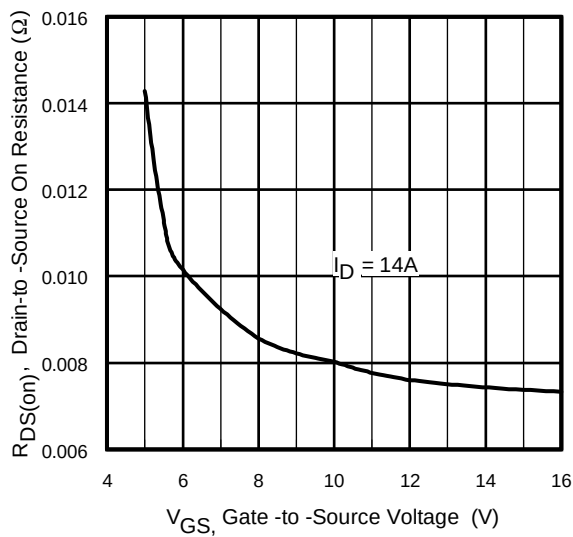


Fig 13. On-Resistance Vs. Gate Voltage

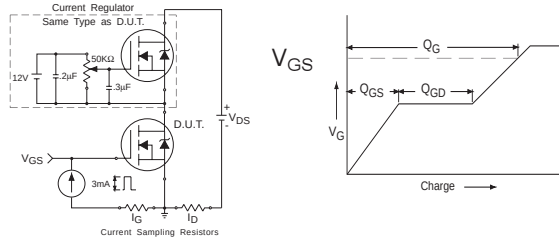


Fig 13a&b. Basic Gate Charge Test Circuit and Waveform

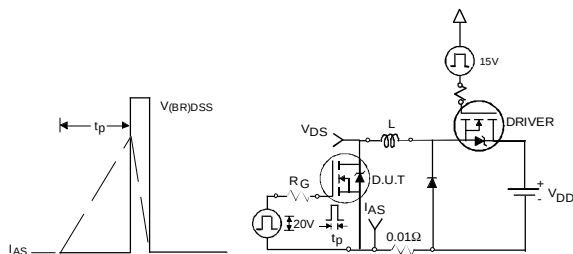


Fig 14a&b. Unclamped Inductive Test circuit and Waveforms

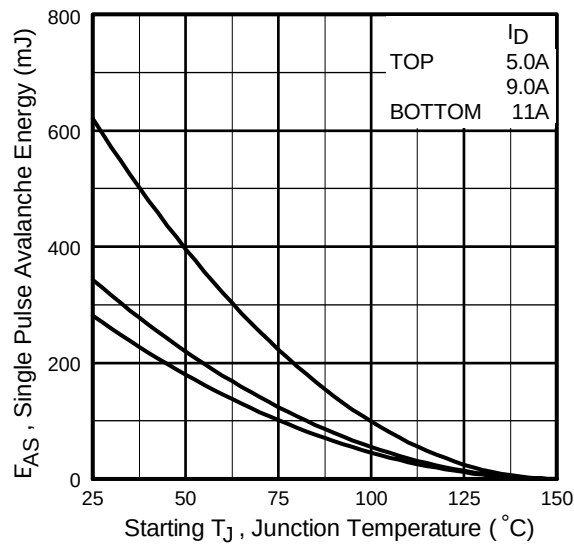
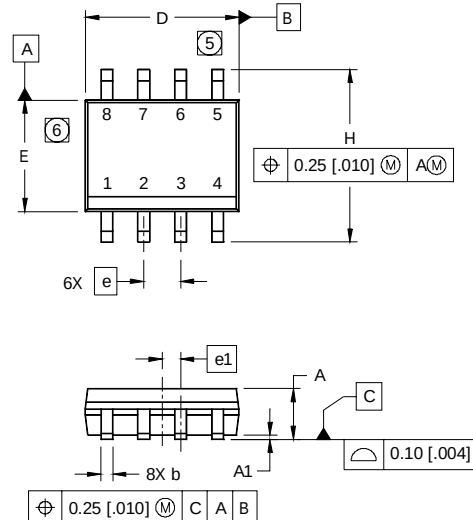


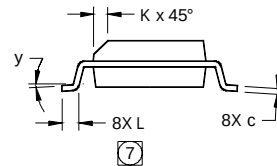
Fig 14c. Maximum Avalanche Energy Vs. Drain Current

SO-8 Package Outline

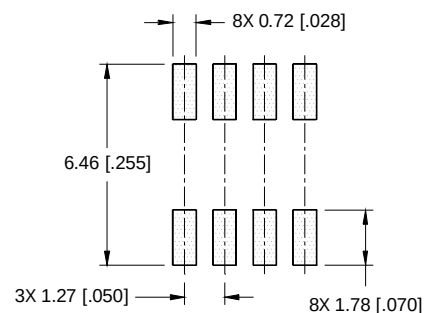
Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



FOOTPRINT

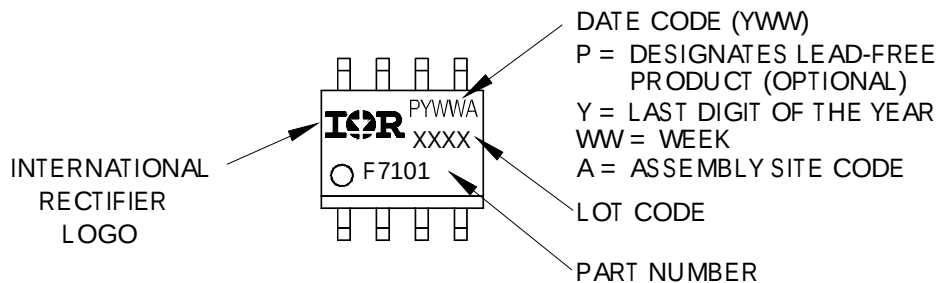


NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

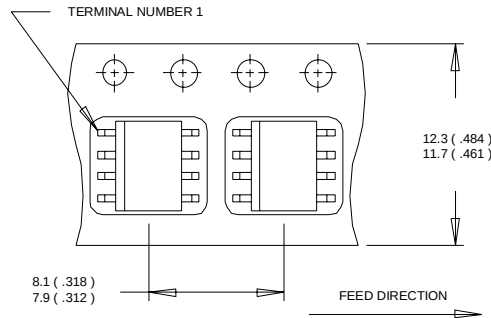


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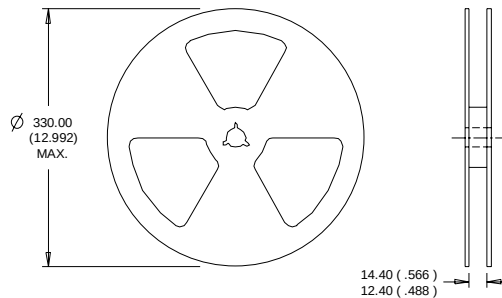
SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)

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- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 4.6\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 11\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board, $t < 10\text{ sec}$

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualifications Standards can be found on IR's Web site.

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